

**CMXT3906**  
**SURFACE MOUNT**  
**DUAL PNP**  
**SILICON TRANSISTORS**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXT3906 type is a dual PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose amplifier and switching applications.

**MARKING CODE: X2A**



**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Continuous Collector Current	$I_C$	200	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^\circ\text{C/W}$

**SYMBOL**

$V_{CBO}$	40	V
$V_{CEO}$	40	V
$V_{EBO}$	5.0	V
$I_C$	200	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**UNITS**

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CEV}$	$V_{CE}=30V, V_{EB}=3.0V$		50	nA
$BV_{CBO}$	$I_C=10\mu A$	40		V
$BV_{CEO}$	$I_C=1.0mA$	40		V
$BV_{EBO}$	$I_E=10\mu A$	5.0		V
$V_{CE(SAT)}$	$I_C=10mA, I_B=1.0mA$		0.25	V
$V_{CE(SAT)}$	$I_C=50mA, I_B=5.0mA$		0.40	V
$V_{BE(SAT)}$	$I_C=10mA, I_B=1.0mA$	0.65	0.85	V
$V_{BE(SAT)}$	$I_C=50mA, I_B=5.0mA$		0.95	V
$h_{FE}$	$V_{CE}=1.0V, I_C=0.1mA$	60		
$h_{FE}$	$V_{CE}=1.0V, I_C=1.0mA$	80		
$h_{FE}$	$V_{CE}=1.0V, I_C=10mA$	100	300	
$h_{FE}$	$V_{CE}=1.0V, I_C=50mA$	60		
$h_{FE}$	$V_{CE}=1.0V, I_C=100mA$	30		
$f_T$	$V_{CE}=20V, I_C=10mA, f=100MHz$	250		MHz
$C_{ob}$	$V_{CB}=5.0V, I_E=0, f=1.0MHz$		4.5	pF
$C_{ib}$	$V_{BE}=0.5V, I_C=0, f=1.0MHz$		10	pF
$h_{ie}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	2.0	12	k $\Omega$

R3 (12-February 2010)

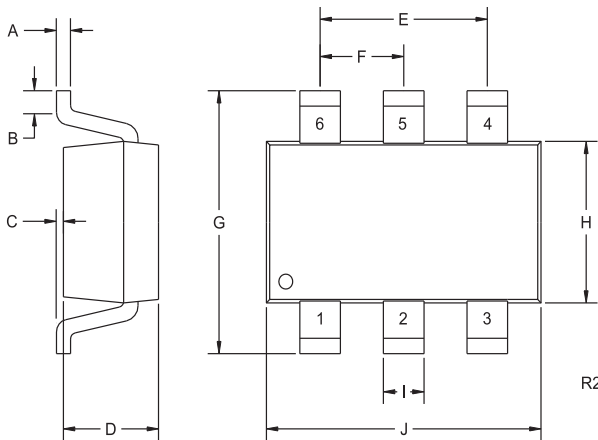
**CMXT3906**  
**SURFACE MOUNT**  
**DUAL PNP**  
**SILICON TRANSISTORS**



**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

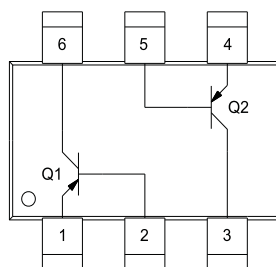
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$h_{re}$	$V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$	0.1	10	$\times 10^{-4}$
$h_{fe}$	$V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$	100	400	
$h_{oe}$	$V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$	3.0	60	$\mu\text{S}$
NF	$V_{CE}=5.0\text{V}$ , $I_C=100\mu\text{A}$ , $R_S=1.0\text{k}\Omega$ , $f=10\text{Hz}$ to $15.7\text{kHz}$		4.0	dB
$t_d$	$V_{CC}=3.0\text{V}$ , $V_{BE}=0.5\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=1.0\text{mA}$		35	ns
$t_r$	$V_{CC}=3.0\text{V}$ , $V_{BE}=0.5\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=1.0\text{mA}$		35	ns
$t_s$	$V_{CC}=3.0\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=I_{B2}=1.0\text{mA}$		225	ns
$t_f$	$V_{CC}=3.0\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=I_{B2}=1.0\text{mA}$		75	ns

**SOT-26 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)



**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

**MARKING CODE: X2A**

R3 (12-February 2010)

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Central Semiconductor:](#)

[CMXT3906 TR PBFREE](#)